

Kyoung-Tae Kim

List of Publications by Year in descending order

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1122
citing authors

#	ARTICLE	IF	CITATIONS
1	Characterization of the Current Mechanisms and Improved Leakage Current in Silver Doped Barium Strontium Titanate. , 2019, , .		0
2	Fabrication of high-aspect-ratio nanoporous high-k MTiO_3 (M= Ba, Sr, or Tj) TiO_3 thin films. Applied Physics Letters, 2017, , .	10.1	50
3	Fabrication of Self-Packaged Seamless Nanoporous SU-8 Microchannels. Journal of Microelectromechanical Systems, 2015, 24, 256-258.	1.7	0
4	Room temperature multiferroic properties of $(\text{Fe}_x, \text{Sr}_{1-x})\text{TiO}_3$ thin films. Applied Physics Letters, 2014, 105, .	1.5	16
5	Microwave characteristics of sol-gel based Ag-doped $(\text{Ba}_{0.6}\text{Sr}_{0.4})\text{TiO}_3$ thin films. Thin Solid Films, 2014, 565, 172-178.	0.8	15
6	Fabrication of an all SU-8 electrospun nanofiber based supercapacitor. Journal of Micromechanics and Microengineering, 2013, 23, 114011.	1.5	12
7	Subwavelength Direct Laser Patterning of Conductive Gold Nanostructures by Simultaneous Photopolymerization and Photoreduction. ACS Nano, 2011, 5, 1947-1957.	7.3	110
8	Fabrication and Characterization of Gold-Polymer Nanocomposite Plasmonic Nanoarrays in a Porous Alumina Template. ACS Nano, 2010, 4, 2249-2255.	7.3	66
9	Characteristics of Nickel-doped Zinc Oxide thin films prepared by sol-gel method. Surface and Coatings Technology, 2008, 202, 5650-5653.	2.2	52
10	Fabrication of submicron structures in nanoparticle/polymer composite by holographic lithography and reactive ion etching. Applied Physics Letters, 2008, 93, 203509.	1.5	6
11	Ferroelectric properties of $\text{Bi}_{3.25}\text{La}_{0.75}\text{Ti}_3\text{O}_{12}$ films using HfO_2 as buffer layers for nonvolatile-memory field-effect transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 1178-1181.	0.9	6
12	Etching Characteristics of $(\text{Na}_{0.5}\text{K}_{0.5})\text{NbO}_3$ Thin Films in an Inductively Coupled Cl_2/Ar Plasma. Ferroelectrics, 2007, 357, 179-184.	0.3	6
13	Dielectric Properties of $(\text{Pb}, \text{Sr})\text{TiO}_3$ Heterolayered Thin Films for Tunable Application. Ferroelectrics, 2007, 357, 211-217.	0.3	0
14	Etch Properties of Hf-Based High-k Dielectrics Using Inductively Coupled Plasma. Ferroelectrics, 2007, 357, 41-47.	0.3	4
15	Dielectric Properties of $(\text{Na}, \text{K})\text{NbO}_3$ Thin Films for Tunable Microwave Device Application. Ferroelectrics, 2007, 356, 166-171.	0.3	4
16	Effect of LaNiO_3 electrode on microstructural and ferroelectric properties of $\text{Bi}_{3.25}\text{Eu}_{0.75}\text{Ti}_3\text{O}_{12}$ thin films. Thin Solid Films, 2007, 515, 8082-8086.	0.8	20
17	Etch damage evaluation on $(\text{Bi}_{4-x}\text{La}_x)\text{Ti}_3\text{O}_{12}$ thin films during the etch process using inductively coupled plasma sources. Materials Science in Semiconductor Processing, 2006, 9, 1108-1114.	1.9	6
18	Electrical and dielectric properties of Ce-doped $\text{Ba}_{0.6}\text{Sr}_{0.4}\text{TiO}_3$ thin films. Surface and Coatings Technology, 2006, 200, 4708-4712.	2.2	35

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19	Dry etching of LaNiO ₃ thin films using inductively coupled plasma. <i>Thin Solid Films</i> , 2006, 506-507, 217-221.	0.8	5
20	Effect of lanthanides-substituted on ferroelectric properties of bismuth titanate thin films prepared by metalorganic decomposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 118, 229-233.	1.7	18
21	The effect of Cr doping on the microstructural and dielectric properties of (Ba _{0.6} Sr _{0.4})TiO ₃ thin films. <i>Thin Solid Films</i> , 2005, 472, 26-30.	0.8	81
22	Plasma etching of (Ba,Sr)TiO ₃ thin films using inductively coupled Cl ₂ /Ar and BCl ₃ /Cl ₂ /Ar plasma. <i>Thin Solid Films</i> , 2005, 475, 86-90.	0.8	17
23	Characterization of BLT thin films using MgO buffer layer for MFIS-FET. <i>Thin Solid Films</i> , 2005, 475, 166-170.	0.8	12
24	The etching properties of MgO thin films in Cl ₂ /Ar gas chemistry. <i>Thin Solid Films</i> , 2005, 475, 313-317.	0.8	11
25	Characterization of ferroelectric Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films prepared by metal organic decomposition method. <i>Thin Solid Films</i> , 2005, 478, 6-12.	0.8	21
26	Correlation between dielectric properties and strain in Pb _{0.5} Sr _{0.5} TiO ₃ thin films prepared by using the sol-gel method. <i>Surface and Coatings Technology</i> , 2005, 190, 190-194.	2.2	13
27	The etching properties of Al ₂ O ₃ thin films in N ₂ /Cl ₂ /BCl ₃ and Ar/Cl ₂ /BCl ₃ gas chemistry. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 118, 201-204.	1.7	20
28	Dry etching of (Ba,Sr)TiO ₃ thin films using an inductively coupled plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005, 23, 894-897.	0.9	6
29	Dry etching of (Pb,Sr)TiO ₃ thin films using inductively coupled plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005, 23, 890-893.	0.9	0
30	Dielectric properties of highly (100) oriented (Pb _{0.5} ,Sr _{0.5})TiO ₃ thin films grown on Si with MgO buffer layer. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004, 22, 2615.	1.6	5
31	Etching mechanism of MgO thin films in inductively coupled Cl ₂ -Ar plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 2101-2106.	0.9	19
32	Ferroelectric properties of lanthanide-doped Pb(Zr _{0.6} ,Ti _{0.4})O ₃ thin films prepared by using a sol-gel method. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 1743-1745.	0.9	6
33	Etching properties of lead-zirconate-titanate thin films in Cl ₂ /Ar and BCl ₃ /Ar gas chemistries. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 1519-1523.	0.9	9
34	Effect of thickness on ferroelectric properties of Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films on Pt/Ti/SiO ₂ /Si substrates. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 1315-1318.	0.9	8
35	(Pb,Sr)TiO ₃ thin films etching characteristics using inductively coupled plasma. <i>Thin Solid Films</i> , 2004, 447-448, 688-692.	0.8	2
36	Dielectric properties of highly (100) oriented (Pb _{0.5} , Sr _{0.5})TiO ₃ thin films grown on LaNiO ₃ electrodes. <i>Thin Solid Films</i> , 2004, 447-448, 651-655.	0.8	21

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37	Structural and electrical properties of metal-ferroelectric-insulator-semiconductor field-effect transistors using a Pt/Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ /CeO ₂ /Si structure. <i>Thin Solid Films</i> , 2004, 447-448, 322-326.	0.8	9
38	Electrical properties of Bi ₄ ^x Eu _x Ti ₃ O ₁₂ (BET) thin films after etching in inductively coupled CF ₄ /Ar plasma. <i>Thin Solid Films</i> , 2004, 447-448, 337-342.	0.8	7
39	Etching mechanism of Bi ₄ ^x La _x Ti ₃ O ₁₂ films in Ar/Cl ₂ inductively coupled plasma. <i>Thin Solid Films</i> , 2004, 447-448, 343-348.	0.8	16
40	Effect of Bi ₄ Ti ₃ O ₁₂ seeding layer on the structural and ferroelectric properties of Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films fabricated by a metalorganic decomposition method. <i>Thin Solid Films</i> , 2004, 447-448, 413-417.	0.8	3
41	Etching Mechanism of Pb(Zr,Ti)O ₃ Thin Films in Cl ₂ /Ar Plasma. <i>Plasma Chemistry and Plasma Processing</i> , 2004, 24, 13-28.	1.1	13
42	Etching mechanisms of (Ba,Sr)TiO ₃ thin films in CF ₄ /Ar inductively coupled plasma. <i>Microelectronic Engineering</i> , 2004, 71, 54-62.	1.1	13
43	Effect of bismuth excess on the crystallization of Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films on Pt/Ti/SiO ₂ /Si substrates. <i>Microelectronic Engineering</i> , 2004, 71, 266-271.	1.1	16
44	Study on the etching damage characteristics of PZT thin films after etching in Cl-based plasma. <i>Microelectronic Engineering</i> , 2004, 71, 294-300.	1.1	9
45	Etching mechanism of (Pb,Sr)TiO ₃ thin films for DRAM application using Cl ₂ /Ar inductively coupled plasma. <i>Vacuum</i> , 2004, 74, 485-489.	1.6	4
46	Low temperature synthesis and ferroelectric properties of (117)-oriented Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films on LaNiO ₃ electrodes. <i>Vacuum</i> , 2004, 74, 665-670.	1.6	7
47	Characteristics of La _{0.5} Sr _{0.5} CoO ₃ thin films fabricated by a simple metal-organic decomposition technique. <i>Vacuum</i> , 2004, 74, 671-675.	1.6	5
48	Etching characteristics and mechanism of Pb(Zr,Ti)O ₃ thin films in CF ₄ /Ar inductively coupled plasma. <i>Vacuum</i> , 2004, 75, 321-329.	1.6	15
49	Improvement in ferroelectric properties of Pt/PZT/Pt capacitors etched as a function of Ar/O ₂ gas mixing ratio into Cl ₂ /CF ₄ plasma. <i>Thin Solid Films</i> , 2004, 459, 71-75.	0.8	6
50	Etching characteristic and mechanism of BST thin films using inductively coupled Cl ₂ /Ar plasma with additive CF ₄ gas. <i>Thin Solid Films</i> , 2004, 459, 127-130.	0.8	8
51	The effect of orientation on structure and ferroelectric properties of Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films. <i>Surface and Coatings Technology</i> , 2004, 177-178, 770-773.	2.2	13
52	Electrical conduction behavior of ferroelectric Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films prepared by a metalorganic decomposition method. <i>Surface and Coatings Technology</i> , 2004, 177-178, 774-778.	2.2	7
53	The effects of drying temperature on the crystallization of YMnO ₃ thin films prepared by sol-gel method using alkoxides. <i>Journal of the European Ceramic Society</i> , 2004, 24, 2613-2617.	2.8	32
54	Characteristics of Pt/Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ /ZrO ₂ /Si structures using ZrO ₂ as buffer layers for ferroelectric-gate field-effect transistors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 1739-1742.	0.9	5

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55	Dry etching characteristics of (Ba _{0.6} Sr _{0.4})TiO ₃ thin films in high density CF ₄ /Ar plasma. Surface and Coatings Technology, 2003, 171, 273-279.	2.2	21
56	Ferroelectric properties of Pb(Zr,Ti)O ₃ heterolayered thin films for FRAM applications. Microelectronic Engineering, 2003, 66, 662-669.	1.1	18
57	Structure and dielectric properties of Bi-doped Ba _{0.6} Sr _{0.4} TiO ₃ thin films fabricated by sol-gel method. Microelectronic Engineering, 2003, 66, 835-841.	1.1	46
58	Plasma-induced damage in PZT thin films etched by inductively coupled plasma. Thin Solid Films, 2003, 435, 222-226.	0.8	20
59	Etch characteristics of (Pb,Sr)TiO ₃ thin films using CF ₄ /Ar inductively coupled plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1616-1619.	0.9	3
60	Etch characteristics of Bi ₄ -xEu _x Ti ₃ O ₁₂ (BET) thin films using inductively coupled plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1475-1481.	0.9	1
61	Large remanent polarization of cerium-modified bismuth-titanate thin films for ferroelectric random access memories. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1376-1380.	0.9	15
62	Study of damage reduction of (Ba _{0.6} Sr _{0.4})TiO ₃ thin films etched in Ar/CF ₄ plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1469-1474.	0.9	8
63	Reduction of etching damage in lead-zirconate-titanate thin films with inductively coupled plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1563-1567.	0.9	8
64	EFFECT OF GRAIN SIZE ON THE FERROELECTRIC PROPERTIES OF Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ Thin Films. International Journal of Modern Physics B, 2002, 16, 4469-4474.	1.0	9
65	The effect of Eu substitution on the ferroelectric properties of Bi ₄ Ti ₃ O ₁₂ thin films prepared by metal-organic decomposition. Thin Solid Films, 2002, 422, 230-234.	0.8	48
66	Recovery of plasma-induced damage in PZT thin film with O ₂ gas annealing. Thin Solid Films, 2001, 398-399, 448-453.	0.8	23
67	Characterization of lead zirconate titanate heterolayered thin films prepared on Pt/Ti/SiO ₂ /Si substrate by the sol-gel method. Thin Solid Films, 2000, 372, 45-49.	0.8	20
68	Comparison of the electrical properties for etched and as-deposited BLT thin films. , 0, , .		0